



United Silicon Carbide, Inc.

Product Qualification Report

Discrete TO-247 Stacked Cascode Devices

Included Products:

TO-247-4L

TO-247-3L

UF3SC065007K4S

UF3SC120016K3S

UF3SC120009K4S

UF3SC120016K4S



This report summarizes the JEDEC qualification results for the 650V and 1200V UF3SC Discrete SiC Cascodes in TO-247-3L and TO-247-4L plastic packages.

The environmental stress tests listed below are performed with pre-stress and post-stress electrical tests. Reviewing the electrical results for new failures and any significant shift in performance satisfies the qualification requirements.

Reliability Stress Test Summary

Test Name	Test Standard	# Samples x # Lots	Failures
High Temperature Reverse Bias (HTRB)	MIL-STD-750-1 M1038 Method A (1000 Hours) $T_J=175^{\circ}\text{C}$, $V=80\% V_{\text{max}}$	26x3 lots 650V & 33x1 lots 1200V	0/111
High Temperature Gate Bias (HTGB)	JESD22 A-108 (1000 Hours) $T_J=175^{\circ}\text{C}$, $V=100\% V_{\text{max}} (+20\text{V})$, bias in one direction	26x3 lots 650V & 33x1 lots 1200V	0/111
High Humidity, High Temperature Reverse Bias (H3TRB)	JESD22-A101C (1000 Hours) $T_A=85^{\circ}\text{C}$, 85% RH, $V_{\text{GS}}=0\text{V}$, $V_{\text{DS}}=100\text{V}$	26x3 lots 650V & 33x1 lots 1200V	0/111
Temperature Cycle (TC)	JESD22 A-104 (1000 Cycles)	26x3 lots 650V & 33x1 lots 1200V	0/111
Autoclave (PCT)	JESD22 A-102 121°C / RH = 100%, 96 hours, 15psig	26x3 lots 650V & 33x1 lots 1200V	0/111
Parametric Verification	Per Datasheet	100% FT x 4 lots	

Physical Dimensions	Per AEC-Q101 Rev D	30x1 packages	0/30
Bondline Thickness	Per Assembly Spec	10x3 lots	0/30
Die Shear	Per Assembly Spec	10x3 lots	0/30
Die Attach Voids	Per Assembly Spec	10x3 lots	0/30
Wire Pull	Per Assembly Spec	10x3 lots	0/30
Wedge Shear	Per Assembly Spec	10x3 lots	0/30
CSAM	Per Assembly Spec	60x3 lots	0/180
Lead Integrity Test	Per AEC-Q101 Rev D	30x1 lots	0/30
Solderability Test	Per AEC-Q101 Rev D	10x1 lots	0/10

Reliability Evaluation:

The FIT rate data presented below is determined according to JEDEC Standard JESD 85 and is determined from the HTRB and HTGB Burn-In sample size.

FIT = 5.427478 failures per billion device hours

MTTF = 21032.83 years

From the equations:

$$\lambda_{hours} = \frac{X^2(\alpha, \nu)}{2 \times D \times H \times A_f}$$

$$FIT = \lambda_{hours} \times 10^9$$

$$MTTF_{hours} = 1/\lambda_{hours}$$

And

$$A_f = e^{\frac{E_a}{k} \left(\frac{1}{T_{use}} - \frac{1}{T_{test}} \right)}$$

Where:



χ^2 = Chi-Squared probability function for a given Confidence Level (α) and Degree of Freedom ($\nu = 2r+2$, where r = the number of failures in the Test Population),

D = Number of Devices in the Test Population,

H = Test Hours per Device,

A_f = Acceleration Factor from the Arrhenius equation,

E_a = Activation Energy (eV),

T_{use} = standardized Use Temperature,

T_{test} = Temperature of Stress Test,

and

k = Boltzmann's Constant.

In our calculations, we used our HTGB and HTRB Burn-In data:

D = 111 devices for HTGB and 111 for HTRB,

H = 1000 hours for HTGB and 1000 hours of HTRB,

$1 - \alpha = 0.6$ (60% Confidence Level)

$r = 0$ Failures

$E_a = 0.7$ eV

$T_{use} = 55$ °C or 328 K

$T_{test} = 175$ °C or 448 K